

Amendments to the Abstract:

Please replace the Abstract on page 11 with the following amended Abstract:

In a single-wafer hot-wall rapid-thermal chemical vapor deposition chamber having a plurality of heating elements, a method of depositing a silicon based film on a wafer comprises the steps of positioning the wafer in the chamber and under the heating elements, applying energy to the plurality of heating elements to heat the wafer to a temperature of up to approximately 550 °C, conveying at least one silicon containing precursor and at least one nitrogen containing precursor, and reacting said silicon and nitrogen containing precursors to deposit a silicon based film on the wafer.~~The present invention provides a single-wafer hot-wall RTCVD system and~~ The method is capable of achieving high deposition rates, preferably of up to and over 1000Å/min, to deposit silicon nitride films or layers (Si₃N₄) ~~using reactants including but not limited to Si₂H₆ with NH₃ at a low temperature~~temperatures of up to approximately 550°C.